

XL1225 (T1225)

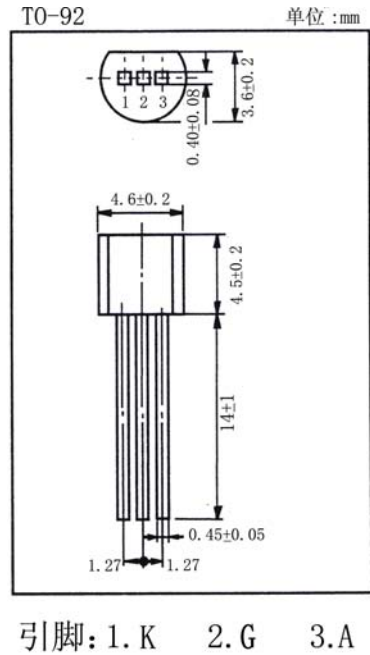
单向可控硅/THYRISTOR

特点：低成本，高容量。

Features: Intended for low cost high volume applications.

极限参数/Absolute maximum ratings (Ta=25°C)

| 参数符号 Symbol | 测试条件 Test condition | 数值 Rating | 单位 Unit |
|----------------------|---|--------------|------------|
| V _{DRM} | T _j =40 to 125°C (r _{gk} =1kΩ) | 400 | V |
| I _T (RMS) | T _c =40°C | 0.8 | A |
| I _T (AV) | Half cycle=180 T _c =40°C | 0.5 | A |
| V _{GRM} | I _{GR} =10 μA | 1.0 | V |
| I _{GM} | 10 μs Max | 0.1 | A |
| P _G (AV) | 20ms Max | 150 | mW |
| T _j | | -40~ 125 | °C |
| T _{STG} | | -40~ 125 | °C |
| T _{SLD} | 1. 6mm from case 10s Max | 250 | °C |



电性能参数/Electrical characteristics (Ta=25°C)

| 参数符号 Symbol | 测试条件 Test condition | 数值 Rating | | | 单位 Unit |
|----------------------------------|--|--------------|------------|------------|------------|
| | | 最小值 Min | 典型值 Typ | 最大值 Max | |
| I _{DRM} | @V _{DRM} (R _{GK} =1KΩ) T _j =125°C | | | 0.1 | mA |
| I _{DRM} | @V _{DRM} (R _{GK} =1KΩ) T _j =25°C | | | 1.0 | μA |
| V _T | AT I _T =0.4A | | | 1.4 | V |
| | AT I _T =0.8A | | | 2.2 | |
| V _T (T ₀) | T _j =125°C | | | 0.95 | V |
| R _t | T _j =125°C | | | 600 | m |
| I _{GT} | V _D =7.0V | | | 200 | μA |
| V _{GT} | V _D =7.0V | | | 0.8 | V |
| I _H | R _{GK} =1KΩ | | | 5 | mA |
| I _L | R _{GK} =1KΩ | | | 6 | mA |

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